

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	10601	TFT or (thin near2 film near2 transistor\$1)	USPA T	2001/09/20 16:59			0
2	BRS	L2	2963	((gate near3 insulat\$4) or (gate near3 dielectric)) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	USPA T	2001/09/20 17:00			0
3	BRS	L3	356	Hydrogen and 1 and 2	USPA T	2001/09/20 16:59			0
4	BRS	L4	478	TFT or (thin near2 film near2 transistor\$1)	US-P GPUB	2001/09/20 17:00			0
5	BRS	L5	155	((gate near3 insulat\$4) or (gate near3 dielectric)) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	US-P GPUB	2001/09/20 16:59			0
6	BRS	L6	36	Hydrogen and 4 and 5	US-P GPUB	2001/09/20 17:00			0
7	BRS	L7	1984	TFT or (thin near2 film near2 transistor\$1)	EPO	2001/09/20 17:01			0
8	BRS	L8	57	((gate near3 insulat\$4) or (gate near3 dielectric)) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	EPO	2001/09/20 17:01			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
9	BRS	L9	0	Hydrogen and 7 and 8	EPO	2001/09/20 17:02		0
10	BRS	L10	11495	TFT or (thin near2 film near2 transistor\$1)	JPO	2001/09/20 17:02		0
11	BRS	L11	526	((gate near3 insulat\$4) or (gate near3 dielectric))same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	JPO	2001/09/20 17:02		0
12	BRS	L12	12	Hydrogen and 10 and 11	JPO	2001/09/20 17:03		0
13	BRS	L13	13363	TFT or (thin near2 film near2 transistor\$1)	DERW ENT	2001/09/20 17:02		0
14	BRS	L14	262	((gate near3 insulat\$4) or (gate near3 dielectric))same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	DERW ENT	2001/09/20 17:03		0
15	BRS	L15	3	Hydrogen and 13 and 14	DERW ENT	2001/09/20 17:03		0